

Andrew

This is Chemistry

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Abstracts

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record for your application

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L3 ANSWER 1 OF 1 HCAPLUS COPYRIGHT 2002 ACS
AN 2000:368652 HCAPLUS
DN 132:351294
TI High-purity tantalum suitable for powder alloying and manufacture of cast recrystallized strip for sputtering targets
IN Michaluk, Christopher A.; Maguire, James D., Jr.; Kawchak, Mark N.; Huber, Louis E., Jr.
PA Cabot Corporation, USA
SO PCT Int. Appl., 54 pp.
CODEN: PIXXD2
DT Patent
LA English
IC ICM C22B034-24
ICS C23C014-34
CC 56-4 (Nonferrous Metals and Alloys)
Section cross-reference(s): 76

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2000031310	A1	20000602	WO 1999-US27832	19991124
W: AE, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CR, CZ, DE, DK, DM, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
RW: GH, GM, KE, LS, MW, SD, SL, SZ, TZ, UG, ZW, AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG				
US 6348113	B1	20020219	US 1998-199569	19981125
EP 1137820	A1	20011004	EP 1999-962850	19991124
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO				
BR 9915674	A	20020122	BR 1999-15674	19991124
JP 2002530534	T2	20020917	JP 2000-584117	19991124
US 2002026965	A1	20020307	US 2001-922815	20010806 <--
PRAI US 1998-199569	A	19981125		
WO 1999-US27832	W	19991124		
AB	The Ta powder is manufd. by redn. of suitable salt (esp. K ₂ TaF ₇) with Na, Mg, or a similar metal, and is purified by electron-beam melting in vacuum chambers lined with refractory metals for the purity .gtoreq.99.995%. The high-purity Ta is suitable for manuf. of recrystd. sputtering targets having the av. grain size .ltoreq.50 .mu.m. The Ta is also suitable for manuf. of elec. capacitors, wires, or resistive film layers for integrated circuits.			
ST	tantalum powder manuf purifn vacuum melting; sputtering target tantalum purity recrystn; elec circuit capacitor manuf tantalum purity			
IT	Refractory metals			
	RL: DEV (Device component use); USES (Uses) (lining, app. with; manuf. of high-purity tantalum powder by salt redn. in high-temp. metal-lined app.)			
IT	Electron beams (melting with; high-purity tantalum powder for melting and manuf. of recrystd. sputtering targets)			
IT	Recrystallization (of tantalum; high-purity tantalum powder for alloying and manuf. of recrystd. sputtering targets)			

IT Capacitors
(tantalum for; high-purity tantalum for manuf. of elec. capacitors and recrystd. sputtering targets)

IT Sputtering
(tantalum; high-purity tantalum powder for alloying and manuf. of recrystd. sputtering targets)

IT 7440-25-7P, Tantalum, preparation
RL: PUR (Purification or recovery); PREP (Preparation)
(high-purity tantalum powder for alloying and manuf. of recrystd. sputtering targets)

IT 7439-89-6, Iron, uses 7439-96-5, Manganese, uses 7440-02-0, Nickel, uses 7440-05-3, Palladium, uses 7440-06-4, Platinum, uses 7440-16-6, Rhodium, uses 7440-18-8, Ruthenium, uses 7440-32-6, Titanium, uses 7440-47-3, Chromium, uses 7440-48-4, Cobalt, uses 7440-58-6, Hafnium, uses 7440-62-2, Vanadium, uses 7440-67-7, Zirconium, uses
RL: DEV (Device component use); USES (Uses)
(lining, app. with; manuf. of high-purity tantalum powder by salt redn. in high-temp. metal-lined app.)

IT 16924-00-8, Potassium fluorotantalate (K₂TaF₇)
RL: PEP (Physical, engineering or chemical process); PROC (Process)
(redn. of; high-purity tantalum powder for alloying and manuf. of recrystd. sputtering targets)

IT 7440-23-5, Sodium, processes
RL: PEP (Physical, engineering or chemical process); PROC (Process)
(redn. with, for tantalum; high-purity tantalum powder for alloying and manuf. of recrystd. sputtering targets)

RE.CNT 10 THERE ARE 10 CITED REFERENCES AVAILABLE FOR THIS RECORD

RE

- (1) Hakko, J; US 4141719 A 1979 HCAPLUS
- (2) Heraeus GmbH W C; EP 0285741 A 1988 HCAPLUS
- (3) Johnson Matthey Elect Inc; WO 9966100 A 1999 HCAPLUS
- (4) Kock, W; JOM 1989, V41(10), P33
- (5) Mitsubishi Kasei Corp; JP 04-178940 A 1992, V016(495), PP-1436
- (6) Nippon Mining Co; WO 8707650 A 1987 HCAPLUS
- (7) Nippon Mining Co; JP 01-290766 A 1989 HCAPLUS
- (8) Toshiba Corp; JP 03-197640 A 1991, V015(461), PC-0887 HCAPLUS
- (9) Wang, G; WO 9961670 A 1999 HCAPLUS
- (10) Willett, W; US 5687600 A 1997

L6 = Ta = tensile axis orientati
L8 = Ta salt.